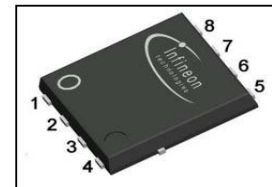


**OptiMOS® 2 Power-Transistor**
**Features**

- Fast switching MOSFET for SMPS
- Optimized technology for notebook DC/DC converters
- Qualified according to JEDEC1 for target applications
- Logic level / N-channel
- Excellent gate charge x RDS(on) product (FOM)
- Very low on-resistance RDS(on)
- Superior thermal resistance
- Avalanche rated
- dv/dt rated
- Pb-free lead plating; RoHS compliant

**Product Summary**

|                  |     |            |
|------------------|-----|------------|
| $V_{DS}$         | 30  | V          |
| $R_{DS(on),max}$ | 5.5 | m $\Omega$ |
| $I_D$            | 73  | A          |

**PG-TDSON-8**


| Type         | Package    | Marking |
|--------------|------------|---------|
| BSC059N03S G | PG-TDSON-8 | 59N03S  |


**Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**

| Parameter                           | Symbol         | Conditions  | Value       | Unit              |
|-------------------------------------|----------------|---|-------------|-------------------|
| Continuous drain current            | $I_D$          | $T_C=25\text{ }^\circ\text{C}$  | 73          | A                 |
|                                     |                | $T_C=100\text{ }^\circ\text{C}$   | 46          |                   |
|                                     |                | $T_A=25\text{ }^\circ\text{C}$ ,<br>$R_{thJA}=45\text{ K/W}^2$  | 17.5        |                   |
| Pulsed drain current                | $I_{D,pulse}$  | $T_C=25\text{ }^\circ\text{C}^{(3)}$  | 200         |                   |
| Avalanche energy, single pulse      | $E_{AS}$       | $I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$   | 150         | mJ                |
| Reverse diode dv/dt                 | dv/dt          | $I_D=50\text{ A}$ , $V_{DS}=24\text{ V}$ ,<br>$di/dt=200\text{ A}/\mu\text{s}$ ,<br>$T_{j,max}=150\text{ }^\circ\text{C}$ | 6           | kV/ $\mu\text{s}$ |
| Gate source voltage                 | $V_{GS}$       |   | $\pm 20$    | V                 |
| Power dissipation                   | $P_{tot}$      | $T_C=25\text{ }^\circ\text{C}$  | 48          | W                 |
|                                     |                | $T_A=25\text{ }^\circ\text{C}$ ,<br>$R_{thJA}=45\text{ K/W}^2$  | 2.8         |                   |
| Operating and storage temperature   | $T_j, T_{stg}$ |   | -55 ... 150 | $^\circ\text{C}$  |
| IEC climatic category; DIN IEC 68-1 |                |   | 55/150/56   |                   |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|  |            |  |   |   |     |     |
|--|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case    | $R_{thJC}$ |  | - | - | 2.6 | K/W |
| Thermal resistance, junction - ambient | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|  |            | 6 cm <sup>2</sup> cooling area <sup>2)</sup> | - | - | 45  |     |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |  |     |     |     |               |
|----------------------------------|---------------|--|-----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                       | 30  | -   | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=35\text{ }\mu\text{A}$                 | 1.2 | 1.6 | 2   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.1 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 10  | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                    | -   | 10  | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=50\text{ A}$                     | -   | 6.9 | 8.6 | m $\Omega$    |
|                                  |               | $V_{GS}=10\text{ V}, I_D=50\text{ A}$                      | -   | 4.6 | 5.5 |               |
| Gate resistance                  | $R_G$         |  | 0.4 | 0.9 | 1.8 | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=50\text{ A}$            | 42  | 84  | -   | S             |

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$<br>$f=1\text{ MHz}$                    | - | 2010 | 2670 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 720  | 950  |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 93   | 140  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=25\text{ A}, R_G=2.7\ \Omega$ | - | 5.7  | 8.5  | ns |
| Rise time                    | $t_r$        |   | - | 4.8  | 7.2  |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 22   | 33   |    |
| Fall time                    | $t_f$        |   | - | 3.8  | 5.7  |    |

**Gate Charge Characteristics<sup>4)</sup>**

|                              |               |   |   |     |     |    |
|------------------------------|---------------|---|---|-----|-----|----|
| Gate to source charge        | $Q_{gs}$      | $V_{DD}=15\text{ V}, I_D=25\text{ A},$<br>$V_{GS}=0\text{ to }5\text{ V}$ | - | 6.3 | 8.4 | nC |
| Gate charge at threshold     | $Q_{g(th)}$   |   | - | 3.2 | 4.3 |    |
| Gate to drain charge         | $Q_{gd}$      |   | - | 4.0 | 6.0 |    |
| Switching charge             | $Q_{sw}$      |   | - | 7.1 | 10  |    |
| Gate charge total            | $Q_g$         |   | - | 15  | 21  |    |
| Gate plateau voltage         | $V_{plateau}$ |   | - | 3.1 | -   |    |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | $V_{DS}=0.1\text{ V},$<br>$V_{GS}=0\text{ to }5\text{ V}$                 | - | 14  | 18  | nC |
| Output charge                | $Q_{oss}$     | $V_{DD}=15\text{ V}, V_{GS}=0\text{ V}$                                   | - | 17  | 23  |    |

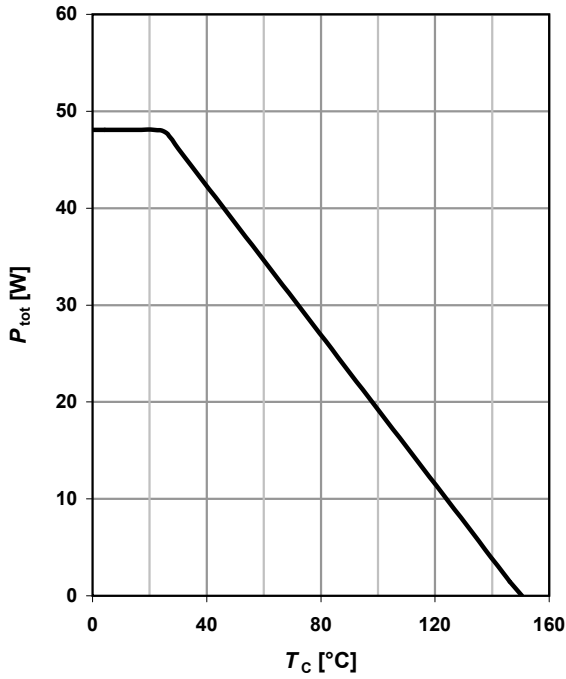
**Reverse Diode**

|                                  |               |   |   |      |     |    |
|----------------------------------|---------------|---|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -    | 48  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -    | 200 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=48\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 0.87 | 1.1 | V  |
| Reverse recovery charge          | $Q_{rr}$      | $V_R=15\text{ V}, I_F=I_S,$<br>$di_F/dt=400\text{ A}/\mu\text{s}$       | - | -    | 10  | nC |

<sup>4)</sup> See figure 16 for gate charge parameter definition

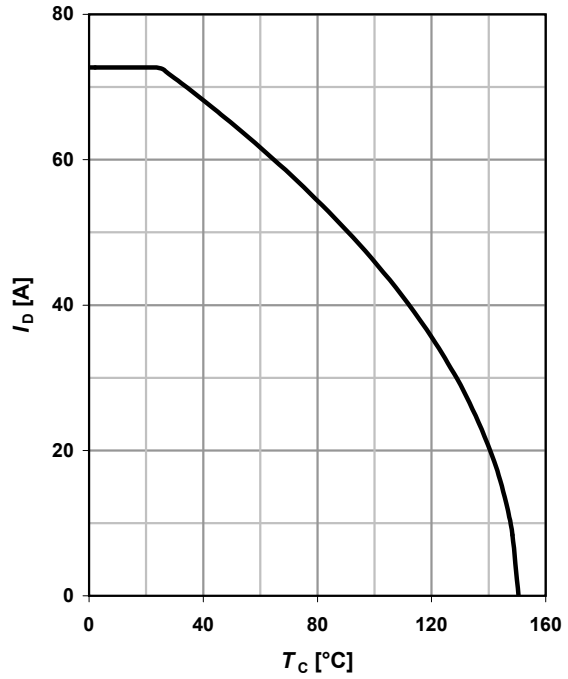
**1 Power dissipation**

$$P_{tot} = f(T_C)$$



**2 Drain current**

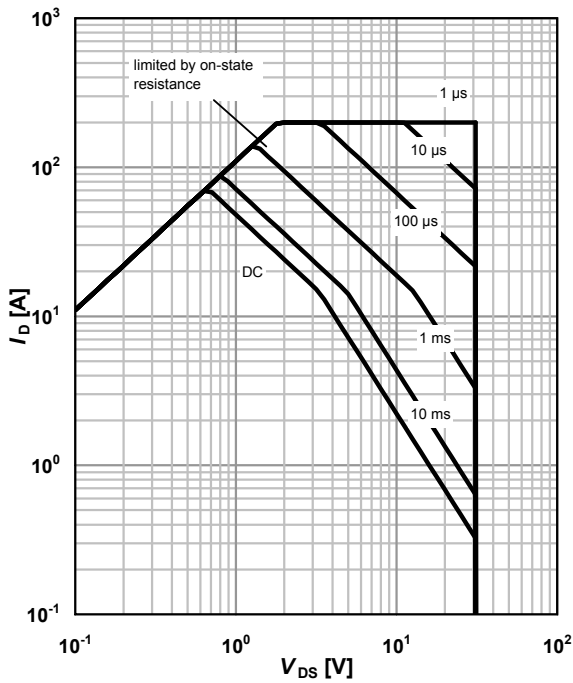
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



**3 Safe operating area**

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

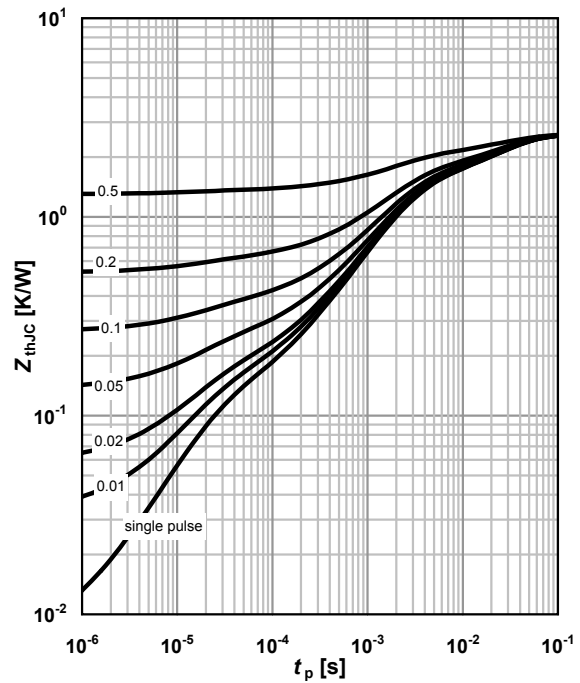
parameter:  $t_p$



**4 Max. transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

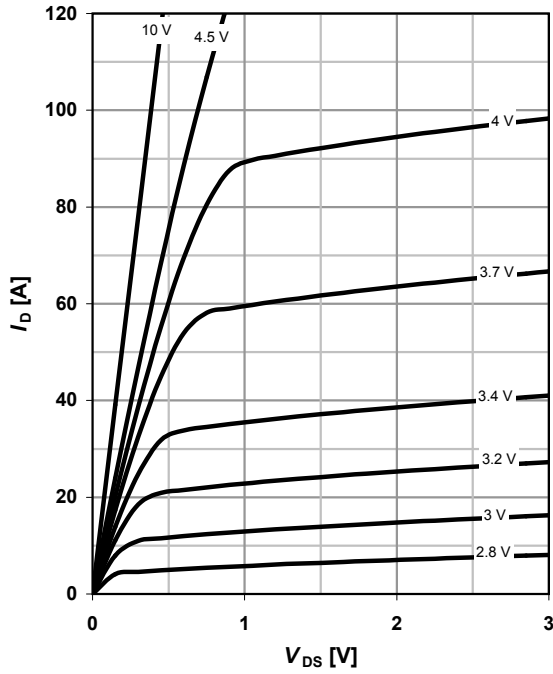
parameter:  $D = t_p / T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

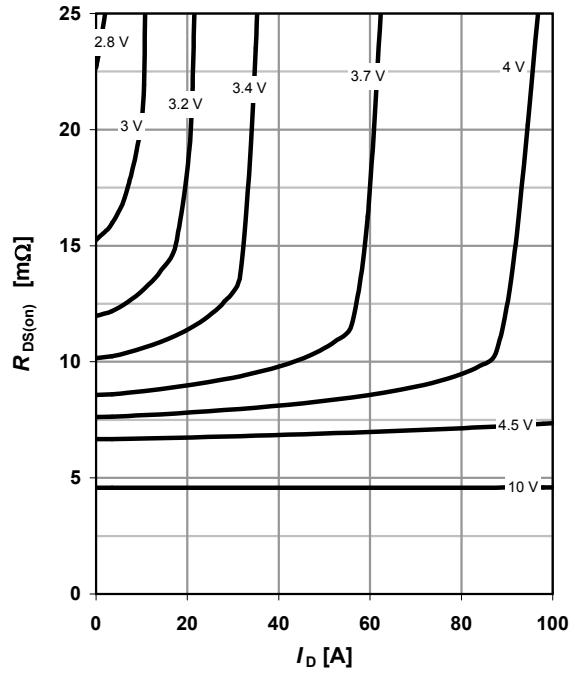
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

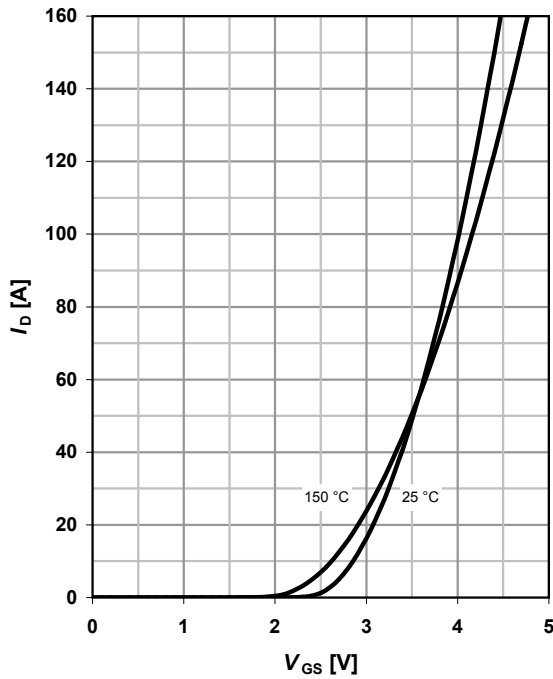
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

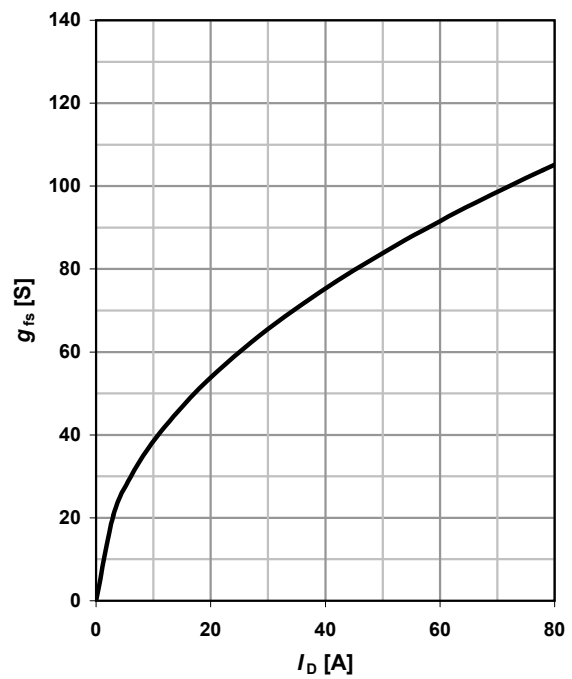
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



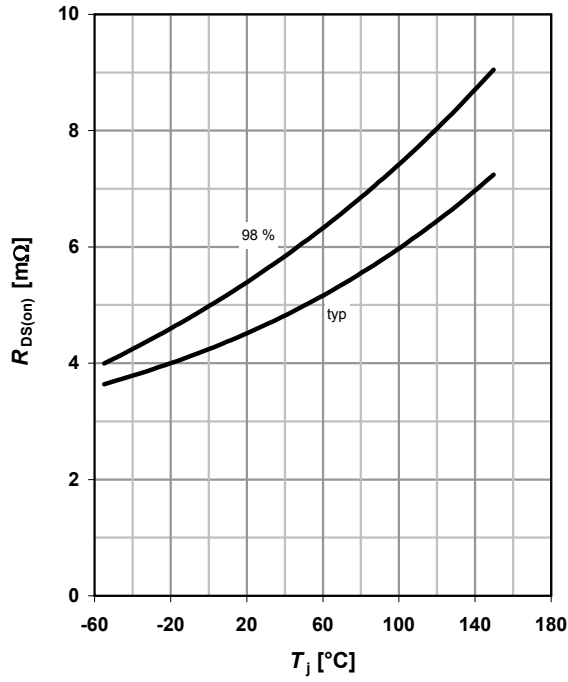
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

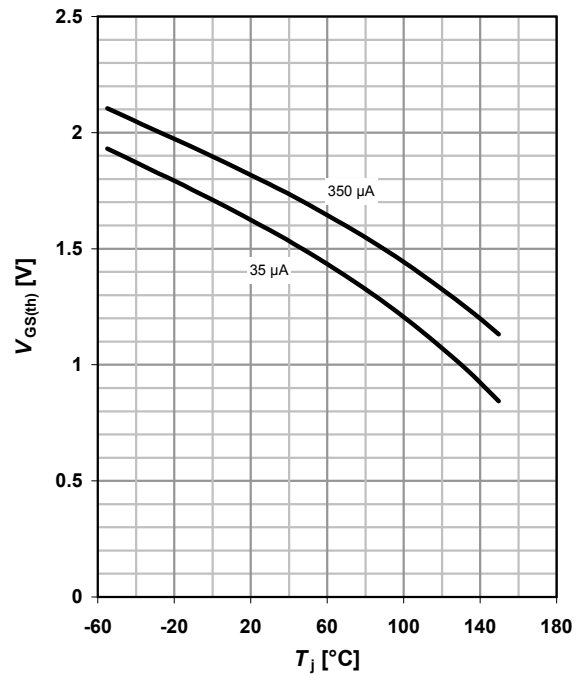
$R_{DS(on)} = f(T_j); I_D = 50 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

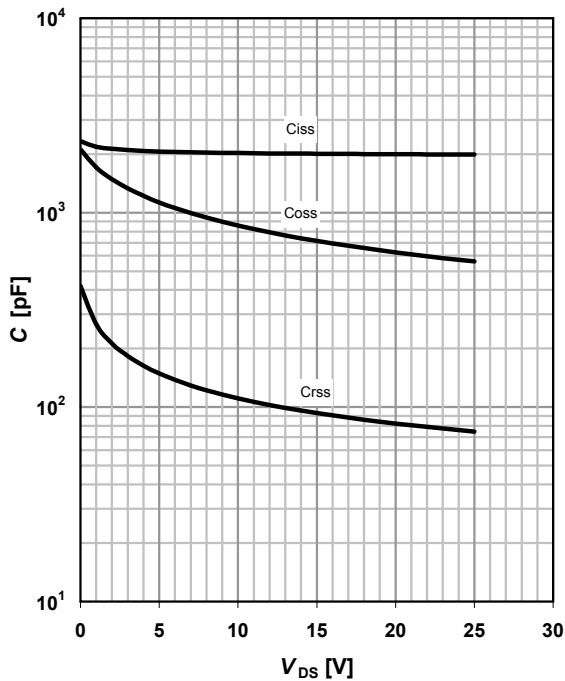
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

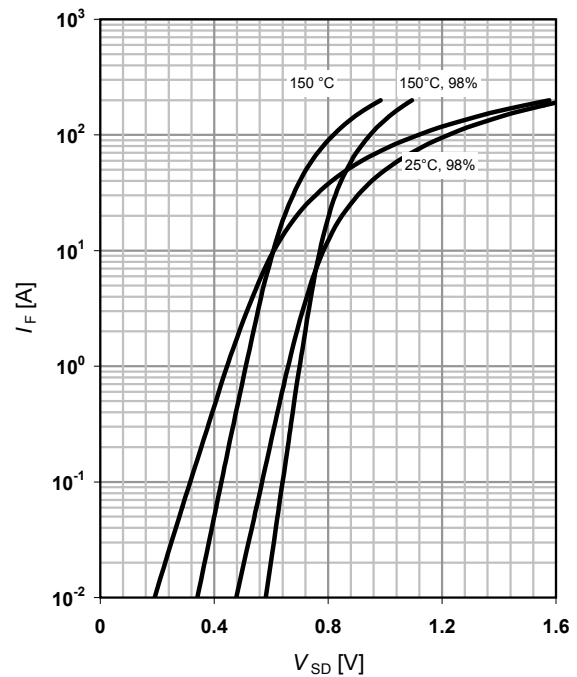
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

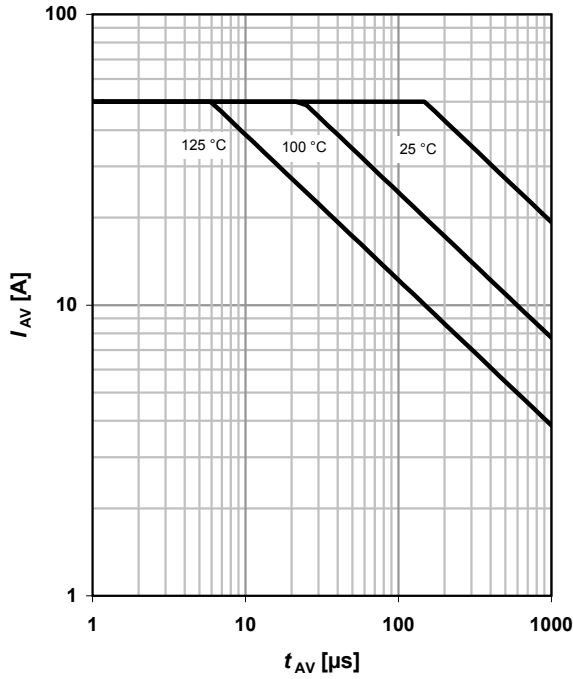
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

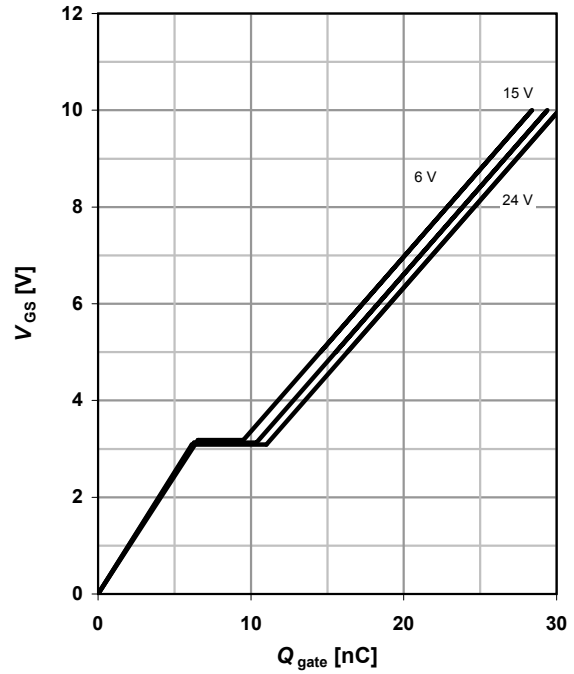
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

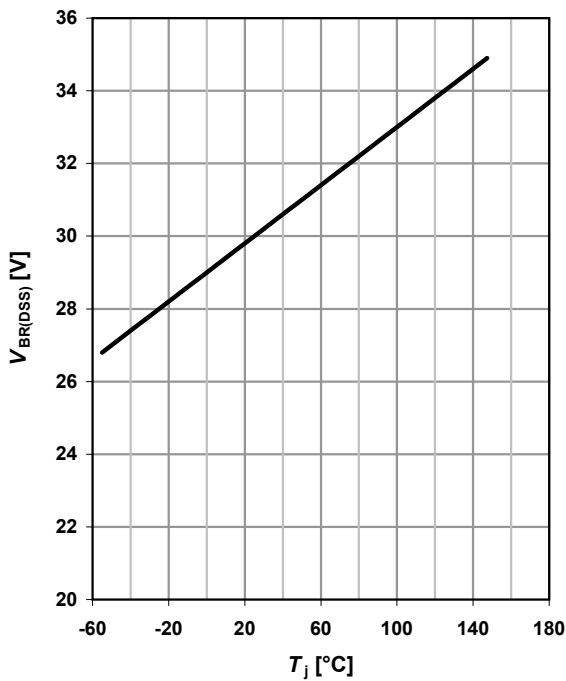
$V_{GS}=f(Q_{gate}); I_D=25 \text{ A pulsed}$

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



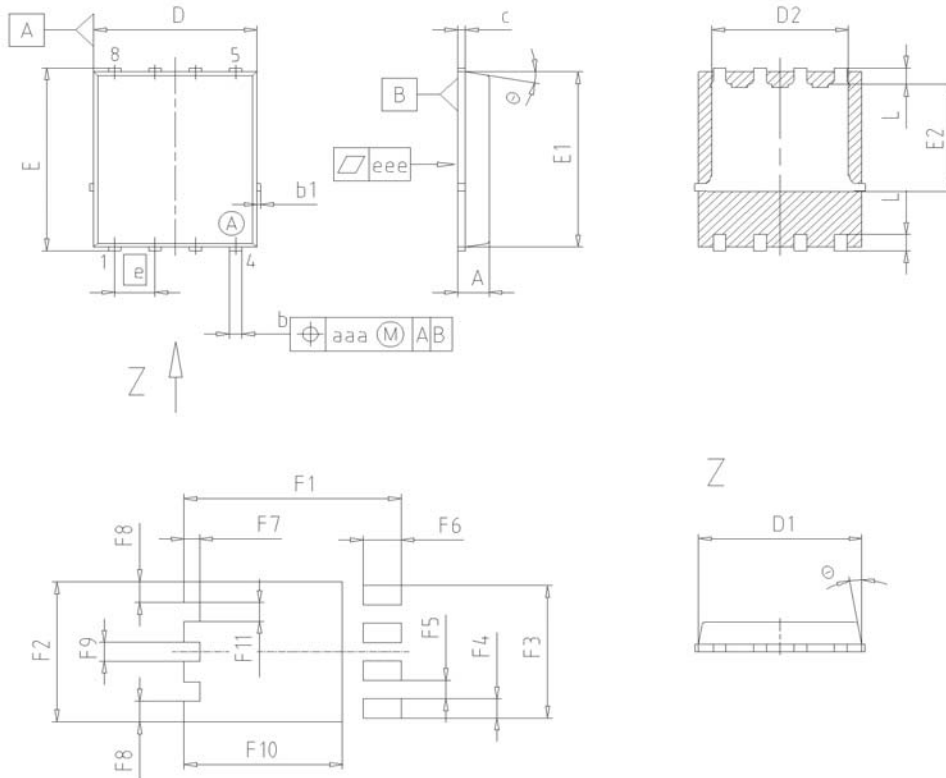
**16 Gate charge waveforms**



Package Outline

PG-TDSON-8

PG-TDSON-8: Outline



| DIM  | MILLIMETERS |      | INCHES     |       |
|------|-------------|------|------------|-------|
|      | MIN         | MAX  | MIN        | MAX   |
| A    | 0.90        | 1.10 | 0.035      | 0.043 |
| b    | 0.34        | 0.54 | 0.013      | 0.021 |
| b1   | 0.02        | 0.22 | 0.001      | 0.008 |
| c    | 0.15        | 0.35 | 0.006      | 0.014 |
| D=D1 | 4.95        | 5.35 | 0.195      | 0.211 |
| D2   | 4.20        | 4.40 | 0.165      | 0.173 |
| E    | 5.95        | 6.35 | 0.234      | 0.250 |
| E1   | 5.70        | 6.10 | 0.224      | 0.240 |
| E2   | 3.40        | 3.80 | 0.134      | 0.150 |
| e    | 1.27        |      | 0.050      |       |
| N    | 8           |      | 8          |       |
| L    | 0.45        | 0.65 | 0.018      | 0.026 |
| □    | 8.5°        |      | 8.5° 11.5° |       |
| aaa  | 0.25        |      | 0.010      |       |
| eee  | 0.05        |      | 0.002      |       |
| F1   | 6.75        | 6.95 | 0.266      | 0.274 |
| F2   | 4.60        | 4.80 | 0.181      | 0.189 |
| F3   | 4.36        | 4.56 | 0.172      | 0.180 |
| F4   | 0.55        | 0.75 | 0.022      | 0.030 |
| F5   | 0.52        | 0.72 | 0.020      | 0.028 |
| F6   | 1.10        | 1.30 | 0.043      | 0.051 |
| F7   | 0.40        | 0.60 | 0.016      | 0.024 |
| F8   | 0.60        | 0.80 | 0.024      | 0.031 |
| F9   | 0.53        | 0.73 | 0.021      | 0.029 |
| F10  | 4.90        | 5.10 | 0.193      | 0.201 |
| F11  | 0.53        | 0.73 | 0.021      | 0.029 |

**DOCUMENT NO.**  
Z8B00003332

**SCALE**

**EUROPEAN PROJECTION**

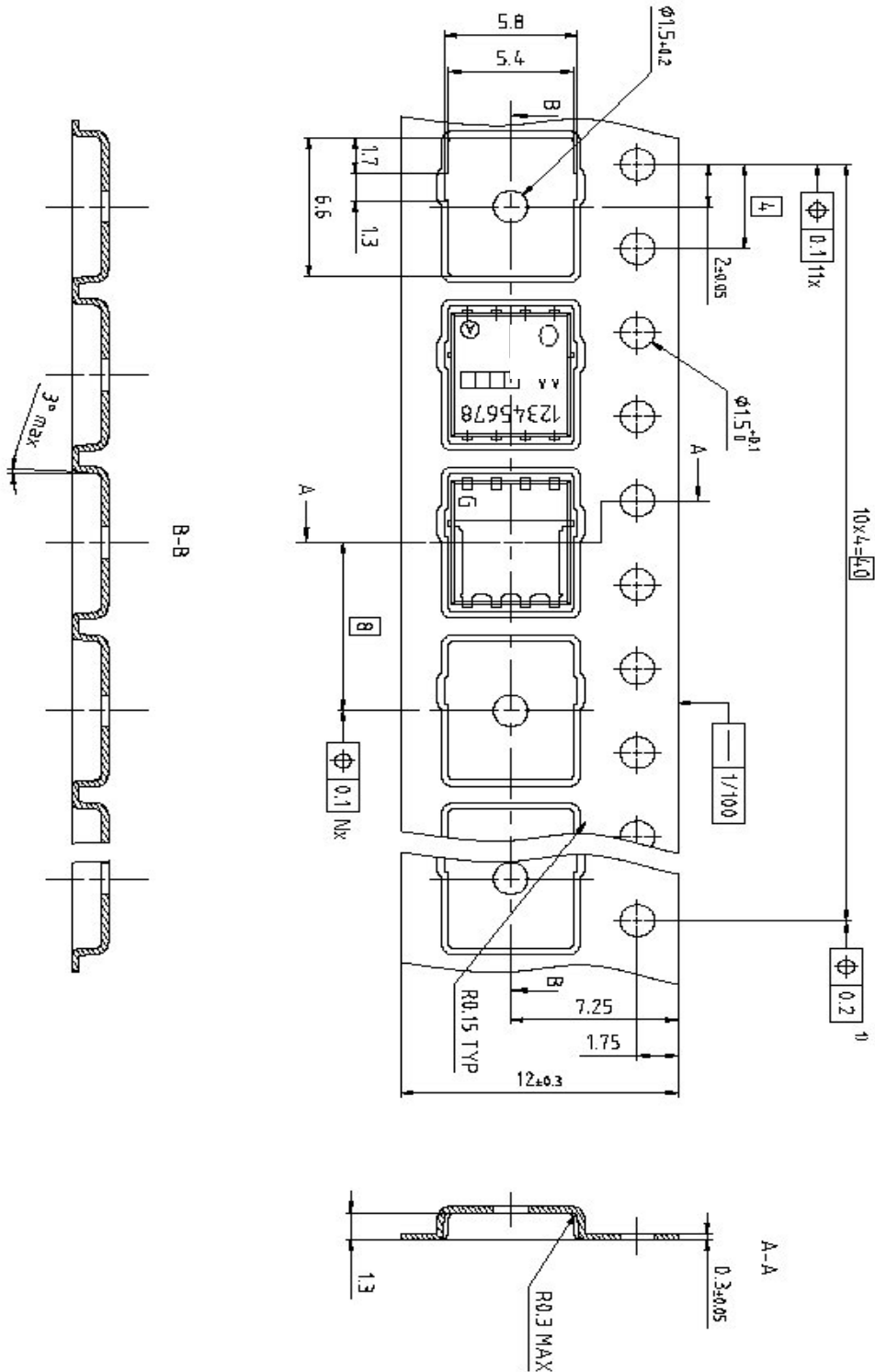
**ISSUE DATE**  
08-03-2007

**REVISION**  
03



Package Outline

PG-TDSON-8: Tape



Dimensions in mm

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